

Zilog

Z08430 Customer
Procurement Spec (CPS)

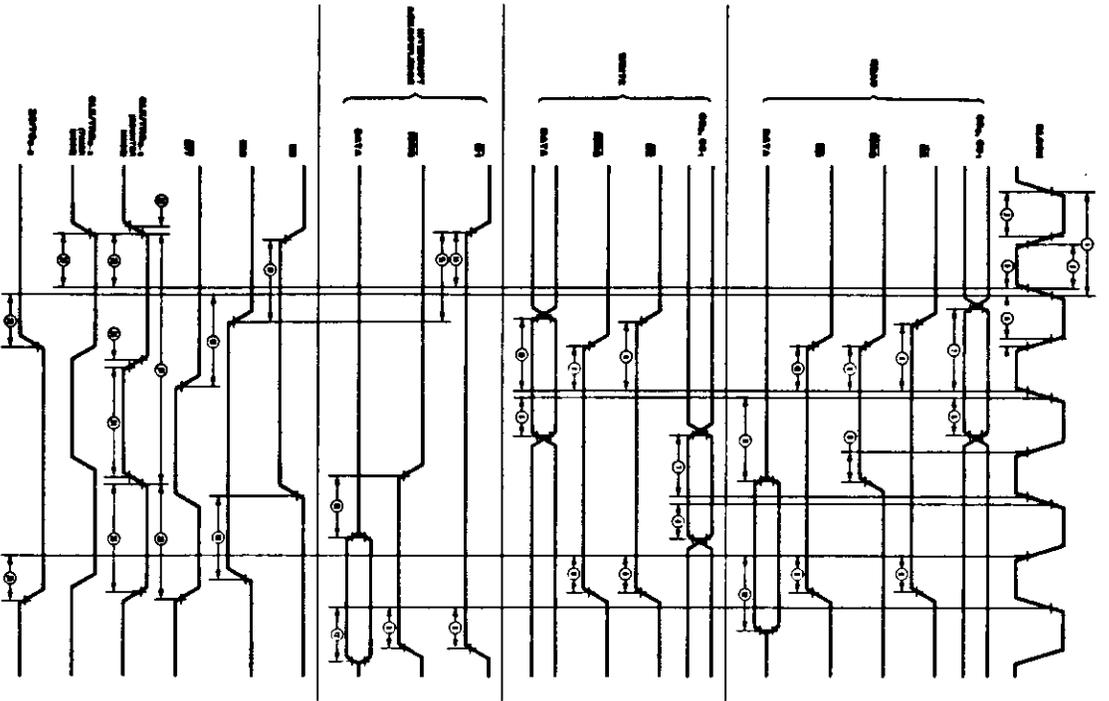
GENERAL DESCRIPTION

The Z80 CTC four-channel counter/timer can be programmed by system software for a broad range of counting and timing applications. The four independently programmable channels of the Z80 CTC satisfy common microcomputer system requirements for event counting, interrupt and interval timing, and general clock rate generation.

System design is simplified because the CTC connects directly to both the Z80 CPU and the Z80 SID with no additional logic. In larger systems, address decoders and buffers may be required.

Programming the CTC is straightforward: each channel is programmed with two bytes; a third is necessary when interrupts are enabled. Once started, the CTC counts down, automatically reloads its time constant, and resumes counting. Software timing loops are completely eliminated. Interrupt processing is simplified because only one vector need be specified; the CTC internally generates a unique vector for each channel.

The Z80 CTC requires a single +5V power supply and the standard Z80 single-phase system clock. It is fabricated with n-channel silicon-gate depletion-load technology and packaged in a 28-pin and a 44-pin chip carrier DIP.

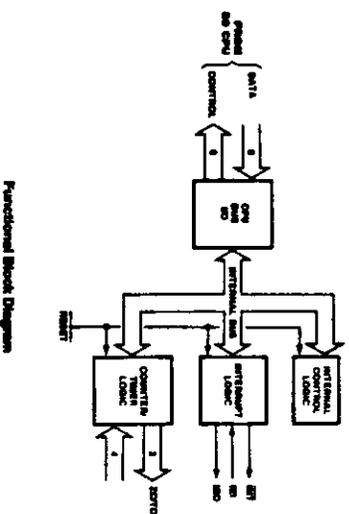


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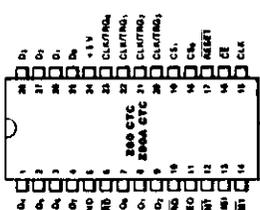
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00-2880-01 Printed in USA

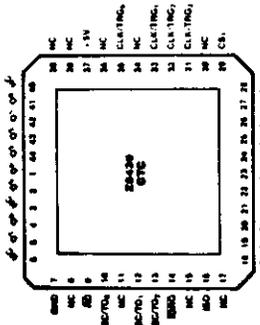


Functional Block Diagram

AC CHARACTERISTICS



48-pin Dual-In-Line Package (DIP)
Pin Assignments



44-pin Chip Carrier, Pin Assignments

DC CHARACTERISTICS

Symbol	Parameter	Min	Max	Unit	Condition
V _{IL}	Clock Input Low Voltage	-0.3 ^a	+0.4 ^b	V	V _{CC} = 2.0 mA
V _{IC}	Clock Input High Voltage	V _{CC} - 0.3 ^a	V _{CC} + 0.3 ^b	V	V _{OH} = -250 μA
V _{IL}	Input Low Voltage	-0.3 ^a	+0.3 ^b	V	V _{IN} = 0.4 to V _{CC}
V _{IH}	Input High Voltage	V _{CC} - 0.3 ^a	V _{CC} + 0.3 ^b	V	V _{OUT} = 0.4 to V _{CC}
V _{OL}	Output Low Voltage	+0.0 ^a	+0.0 ^b	V	V _{OH} = 1.5 V
V _{OH}	Output High Voltage	+2.0 ^a	+2.0 ^b	V	I _{OUT} = 3000
I _{CC}	Power Supply Current		+120 ^a	μA	
I _L	Input Leakage Current		± 10 ^a	μA	
I _{OD}	3-State Output Leakage Current in High		± 10 ^a	μA	
I _{OD}	3-State Output Leakage Current in Low		-1.0 ^a	μA	

^a Tested
^b Guaranteed by Design
^c Guaranteed by Characterization

Number	Symbol	Parameter	200k CTC	300k CTC	400k CTC	500k CTC	Notes
			Min	Max	Min	Max	
1	T _{CC}	Clock Cycle Time	400	(1)	250	(1)	165 [1]
2	T _{WCH}	Clock Width (High)	170	2000	105	2000	65 2000
3	T _{WCL}	Clock Width (Low)	170	2000	105	2000	65 2000
4	T _{IC}	Clock Fall Time	30	30	30	30	20
5	T _{IC}	Clock Rise Time	30	30	30	30	20
6	T _H	All Hold Times	0	0	0	0	0
7	T _{CS(C)}	CS to Clock Setup Time	160	160	160	160	100
8	T _{CE(C)}	CE to Clock Setup Time	200	200	150	100	100
9	T _{RD(C)}	RD to Clock Setup Time	250	250	115	70	70
10	T _{RD(C)}	RD to Clock Setup Time	240	240	115	70	70
11	T _{RD(O)}	RD to Data Out Delay					130 [2]
12	T _{RD(O)}	RD to Data Out Delay					90
13	T _{RD(C)}	Data in to Clock Setup Time	60	60	60	40	40
14	T _{RD(C)}	DT to Clock Setup Time	210	210	80	70	70
15	T _{RD(C)}	DT to RD Delay (pin-to-pin, internally preceding M1)					
16	T _{RD(O)}	RD to Data Out Delay (M1, C, pin)	340	340	160	110	110 [2]
17	T _{RD(O)}	RD to RD Delay	180	180	130	100	100 [2]
18	T _{RD(O)}	RD to RD Delay (After ED Decoding)	220	220	180	110	110 [2]
19	T _{RD(O)}	RD to RD Delay (Clock to RD)	(1) × 200	(1) × 140	(1) × 140	(1) × 120	[4, 5]
20	T _{RD(O)}	RD to RD Delay (RD to RD)	(18) × (28)	(18) × (28)	(18) × (28)	(18) × (28)	[5, 6]
		RD to RD Delay (RD to RD)	(1) × (18) × (28)	(1) × (18) × (28)	(1) × (18) × (28)	(1) × (18) × (28)	[5, 6]
21	T _{RD(O)}	RD to RD Delay	210	210	210	210	[5]
22	T _{RD(O)}	RD to RD Delay	50	50	50	40	40
23	T _{RD(O)}	RD to RD Delay	50	50	50	40	40
24	T _{RD(O)}	RD to RD Delay	200	200	200	120	120
25	T _{RD(O)}	RD to RD Delay	200	200	200	120	120
26	T _{RD(O)}	RD to RD Delay	300	300	210	160	160
27	T _{RD(O)}	RD to RD Delay	300	300	210	160	160
28	T _{RD(O)}	RD to RD Delay	210	210	210	160	160
29	T _{RD(O)}	RD to RD Delay	180	180	180	160	160

¹ T_{CC} = T_{WCH} + T_{WCL} + T_{IC}
² Increase delay by 10 ns for each 50 pF increase in loading, 200 pF maximum for data lines and 100 pF for control lines
³ Increase delay by 2 ns for each 10 pF increase in loading, 100 pF maximum
⁴ Tested
⁵ Counter mode
⁶ Counter mode

Parasitic numbers reference the data number of a parameter e.g. (1) refers to T_{CC}
T_{RD(O)} > (M1 - 2) × (28) × (28) + T_{RD(O)} + T_{IC} + T_{IC} + T_{IC}
Delay / duty: RESET must be active for a minimum of 3 clock cycles
Use the characteristics unless otherwise specified

Clock-cycle time-dependent characteristics. See footnotes to AC Characteristics.
Loadings are preliminary and subject to change. Units in parentheses are tested
Guaranteed by Design
Guaranteed by Characterization